



America Semiconductor

Silicon Super Fast Recovery Diode

MURTA60020 thru MURTA60060R

$V_{RRM} = 200\text{ V} - 600\text{ V}$

$I_F = 600\text{ A}$

Features

- High Surge Capability
- Types up to 600 V V_{RRM}

Heavy Three Tower Package



Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MURTA60020 (R)	MURTA60040 (R)	MURTA60060 (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		50	100	200	V
RMS reverse voltage	V_{RMS}		35	71	141	V
DC blocking voltage	V_{DC}		50	100	200	V
Continuous forward current	I_F	$T_C \leq 100\text{ }^\circ\text{C}$	600	600	600	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ }^\circ\text{C}$, $t_p = 8.3\text{ ms}$	4400	4400	4400	A
Operating temperature	T_j		-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$

Electrical characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	MURTA60020 (R)	MURTA60040 (R)	MURTA60060 (R)	Unit
Diode forward voltage	V_F	$I_F = 300\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$	1.3	1.5	1.7	V
Reverse current	I_R	$V_R = 50\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$	25	25	25	μA
		$V_R = 50\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$	5	5	5	mA
Recovery Time						
Maximum reverse recovery time	T_{RR}	$I_F = 0.5\text{ A}$, $I_R = 1.0\text{ A}$, $I_{RR} = 0.25\text{ A}$	200	220	280	nS
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}		0.12	0.12	0.12	$^\circ\text{C/W}$



Figure .1- Typical Forward Characteristics

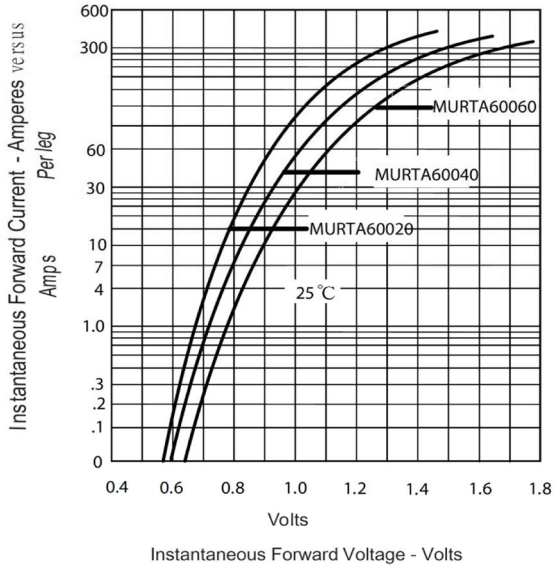


Figure .2- Forward Derating Curve

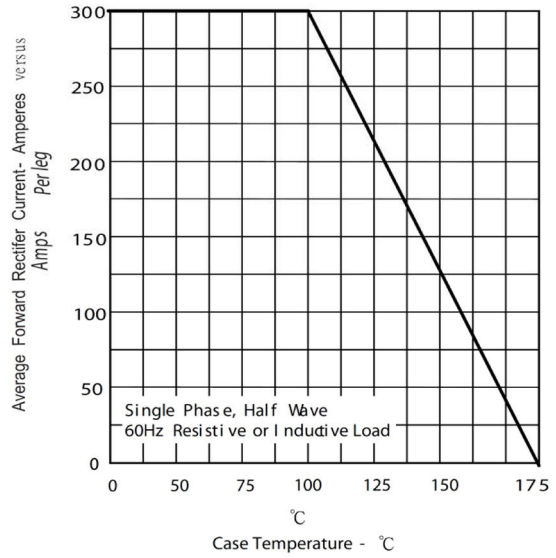


Figure.3-Peak Forward Surge Current

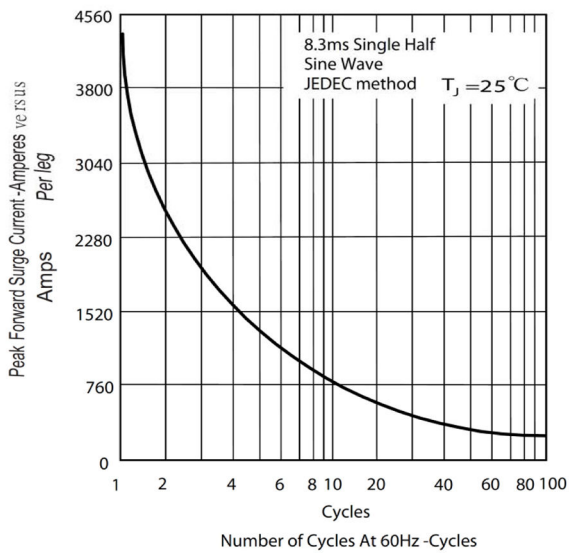


Figure .4-Typical Reverse Characteristics

